



LOW V_{CE(SAT)} NPN SURFACE MOUNT TRANSISTOR

Features

- Ideal for Medium Power Amplification and Switching
- Complementary PNP Type Available (DSS20200L)
- Ultra Low Collector-Emitter Saturation Voltage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)





B E Device Schematic

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V _{EBO}	6	V
Peak Pulse Current	I _{CM}	4	Α
Continuous Collector Current	Ic	2	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 3) @ T _A = 25°C	$R_{ hetaJA}$	209	°C/W
Power Dissipation (Note 4) @ T _A = 25°C	P_{D}	1.2	mW
Thermal Resistance, Junction to Ambient Air (Note 4) @ T _A = 25°C	$R_{ hetaJA}$	104	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on FR-4 PCB with minimum recommended pad layout.
- 4. Device mounted on FR-4 PCB with 1 inch² copper pad layout.



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	V _{(BR)CBO}	20		_	V	$I_C = 100 \mu A$	
Collector-Emitter Breakdown Voltage (Note 5)	V _{(BR)CEO}	20		_	V	$I_C = 10mA$	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6		_	V	$I_E = 100 \mu A$	
Collector-Base Cutoff Current	I _{CBO}	_	_	100	nA	$V_{CB} = 20V, I_E = 0$	
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 6V, I_{C} = 0$	
ON CHARACTERISTICS (Note 5)							
		200	_	_		$V_{CE} = 2V$, $I_C = 10mA$	
DC Current Gain	h	200	330	_		$V_{CE} = 2V, I_{C} = 500mA$	
DC Current Gain	h _{FE}	200		_		$V_{CE} = 2V$, $I_C = 1A$	
		200		_		$V_{CE} = 2V$, $I_C = 2A$	
		_	_	10		$I_C = 0.1A, I_B = 10mA$	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	40	50	mV	$I_C = 1.0A$, $I_B = 100mA$	
Collector-Emitter Saturation voltage		_	75	90	IIIV	$I_C = 1.0A, I_B = 10mA$	
		_	70	100		$I_C = 2.0A$, $I_B = 200mA$	
Equivalent On-Resistance	R _{CE(SAT)}	_	35	50	mΩ	$I_E = 2A$, $I_B = 200mA$	
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	_	0.9	V	$I_C = 1A, I_B = 10mA$	
Base-Emitter Turn-on Voltage	V _{BE(ON)}	_	_	0.9	V	$V_{CE} = 2V$, $I_C = 1A$	
SMALL SIGNAL CHARACTERISTICS							
Transition Frequency	f⊤	150	_	_	MHz	$V_{CE} = 5V, I_{C} = 100mA,$ f = 100MHz	
Output Capacitance	C_{obo}	_	_	45	pF	$V_{CB} = 3V, f = 1MHz$	
Input Capacitance	C _{ibo}	_	_	450	pF	$V_{EB} = 0.5V, f = 1MHz$	
SWITCHING CHARACTERISTICS							
Turn-On Time	ton	_	_	200	ns	$V_{CC} = 15V, I_C = 750mA,$	
Delay Time	t _d	_	_	100	ns	$I_{B1} = 15\text{mA}$	
Rise Time	t _r		_	100	ns	IRI - IOIIIV	
Turn-Off Time	t _{off}	_		610	ns	\\\\ 15\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Storage Time	t _s	_	_	500	ns	$V_{CC} = 15V, I_C = 750mA,$	
Fall Time	t _f	_	_	110	ns	$I_{B1} = I_{B2} = 15$ mA	

Notes: 5. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.

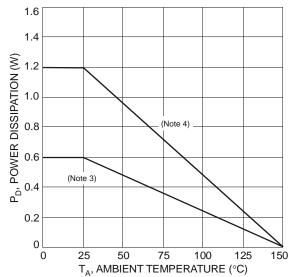
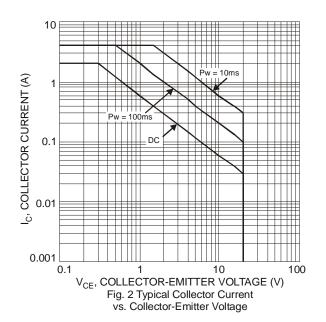
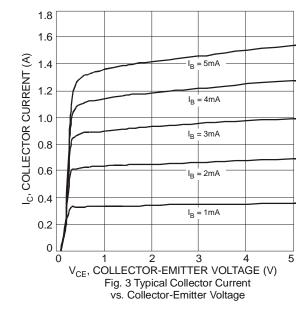
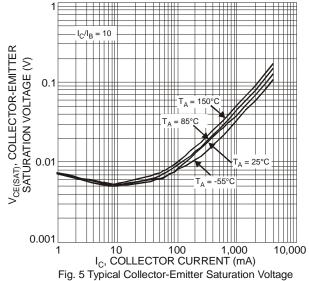


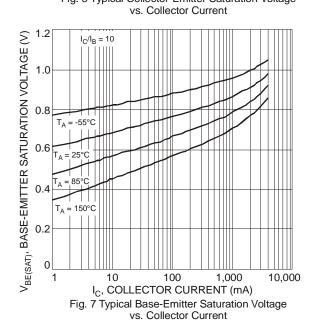
Fig. 1 Power Dissipation vs. Ambient Temperature

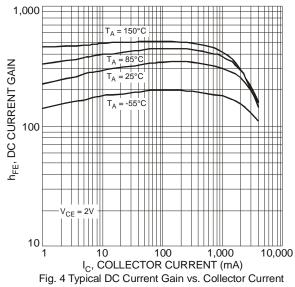


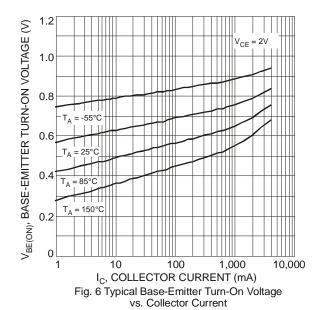












1,000 CAPACITANCE (pF) 100 10 0.1 10 100 V_R, REVERSE VOLTAGE (V)

Fig. 8 Typical Capacitance Characteristics



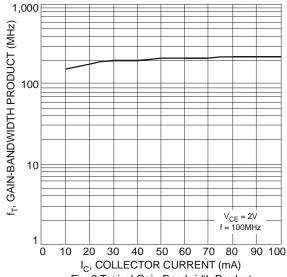


Fig. 9 Typical Gain-Bandwidth Product vs. Collector Current

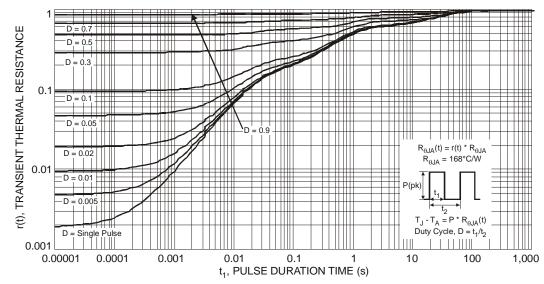


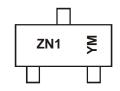
Fig. 10 Transient Thermal Response

Ordering Information (Note 6)

Part Number	Case	Packaging
DSS20201L-7	SOT-23	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



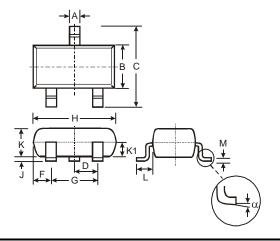
ZN1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

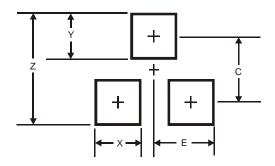


Package Outline Dimensions



	SOT-23					
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
M	0.085	0.18	0.11			
α	0°	8°	-			
All	All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
Е	1.35

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